GOSTONE

RoHS COMPLIANT

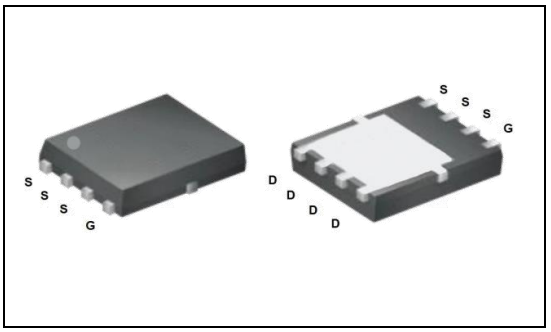
N-Channel 40V,3.2mΩ max,SGT Power MOSFET

GMS032N04F1

Product Summary

V_{DS} (V)	$R_{DS(on),max}$ (mΩ)	I_D (A)
40	3.2 @ V_{GS} = 10V	87 (1)

PDFN5060

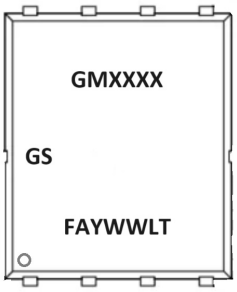


Features

- Low $R_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

Application

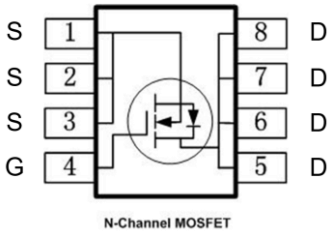
- DC/DC conversion
- Power switch
- Motor drives
- Li- Battery Protection



PDFN5060

NOTE:
LOGO - GS
GMXXXXX- Part number code
F - Fab location code
A - Assembly location code
Y - Year code
WW - Week code
L&T - Assembly lot code

Equivalent circuit



Absolute maximum rating@25℃

Parameter		Symbol	Limit	Unit
Drain-source voltage		V_{DS}	40	V
Gate-source voltage		V_{GS}	±20	
Continuous drain current	T_C=25℃(1)	I_D	87	A
	T_C=100℃(1)		53	
Pulsed drain current(2)		$I_{D,pulse}$	348	
Avalanche energy, single pulse(3)		E_{AS}	194	mJ
Power dissipation	T_C=25℃	P_D	74	W
	T_A=100℃		29	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to 150	℃

Thermal Characteristic

Parameter		Symbol	Max.	Unit
Thermal resistance, junction-to-case	Steady state	$R_{\theta JC}$	1.7	℃/W
Thermal resistance, junction-to-ambient (4)	Steady state	$R_{\theta JA}$	26	

Electrical Characteristics (TJ=25℃ unless otherwise noted)

Parameter	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Static parameter						
Drain to source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0, I_D = 250 μA	40			V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 μA	1.2	1.7	2.5	V
Gate-body leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V			1	μA
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 20 A		2.6	3.2	mΩ
Forward transconductance (5)	g_{fs}	V_{DS} = 5 V, I_D = 30 A		23		S
Gate resistance	R_g	f = 1 MHz		4.2		Ω
Dynamic(5)						
Total gate charge V_{GS} = 10V	Q_g	V_{DS} = 20 V, I_D = 20 A, V_{GS} = 10 V		18		nC
Total gate charge V_{GS} = 6.0V	Q_g			10.9		
Gate-source charge	Q_{gs}			5.6		
Gate-drain charge	Q_{gd}			2.5		
Turn-on delay time	$t_{d(on)}$	V_{DS} = 20 V, I_D = 20 A, V_{GS} = 10 V, R_{GEN} = 3 Ω		4.4		ns
Rise time	t_r			3.8		
Turn-off delay time	$t_{d(off)}$			18		
Fall time	t_f			8.6		
Input capacitance	C_{iss}	V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz		1605		pF
Output capacitance	C_{oss}			955		
Reverse transfer capacitance	C_{rss}			40		
Reverse Diode Characteristics (5)						
Diode forward voltage	V_{SD}	V_{GS} = 0 V, I_F = 2 A		0.7	1.2	V
Reverse recovery time	t_{rr}	I_F = 20 A, di/dt = 100 A/μs		48		ns
Reverse recovery charge	Q_{rr}			18		nC

Notes

(1) Limited by maximum junction temperature.

(2) Pulse width limited by maximum junction temperature.

(3) V_{DS} = 20 V, V_{GS} = 10 V, L = 1.0 mH.

(4) Device mounted on FR-4 substrate PC board with 2oz copper in 1inch square cooling area.

(5) Guaranteed by design, not subject to production testing.

Typical Performance Characteristics

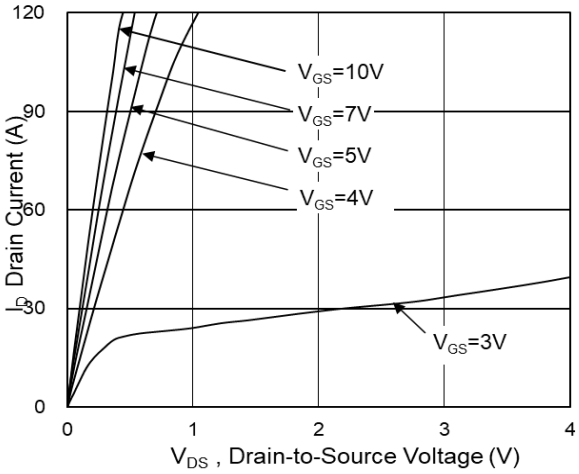


Fig.1 Typical Output Characteristics

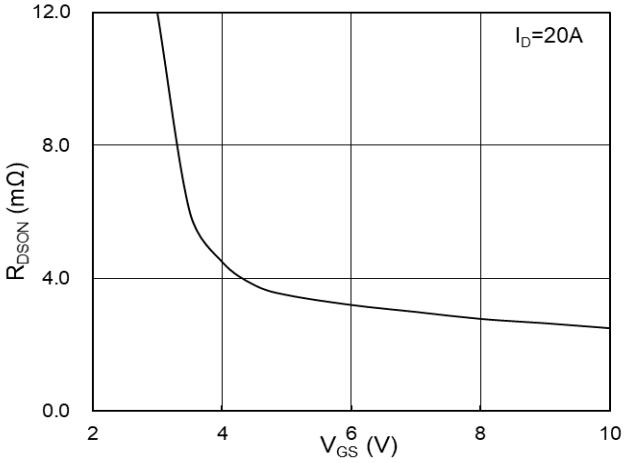


Fig.2 On-Resistance vs G-S Voltage

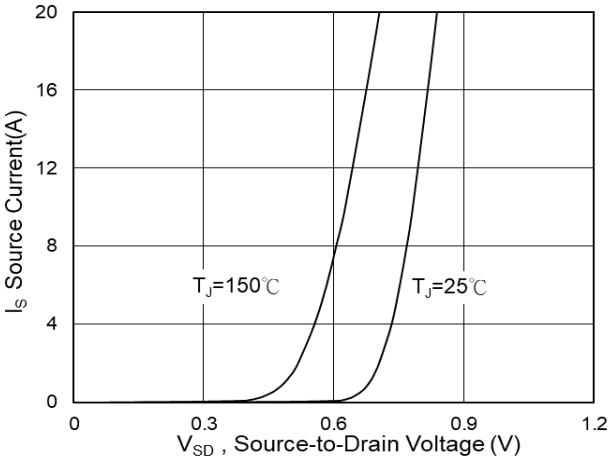


Fig.3 Source Drain Forward Characteristics

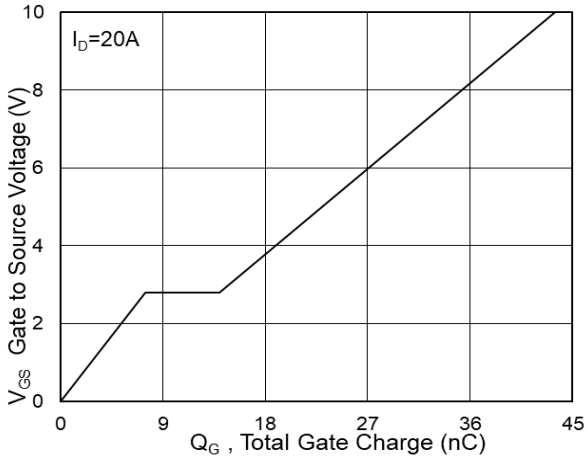


Fig.4 Gate-Charge Characteristics

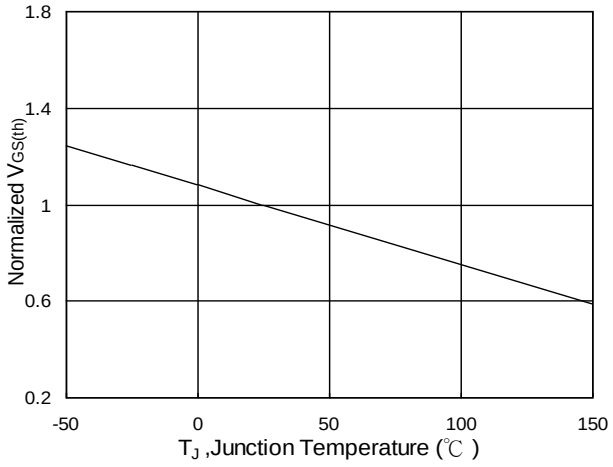


Fig.5 Normalized $V_{GS(th)}$ vs T_J

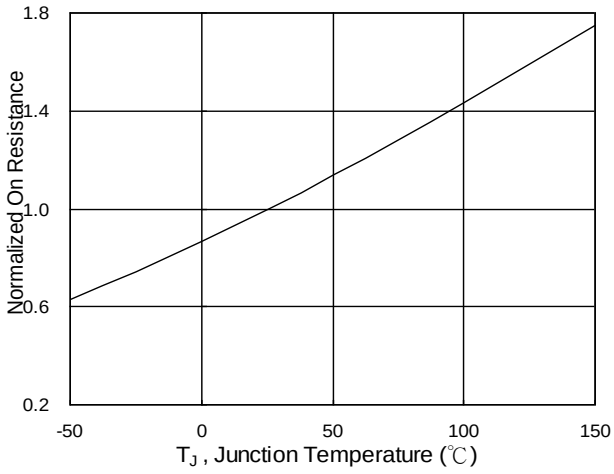


Fig.6 Normalized R_{DSON} vs T_J

Typical Performance Characteristics

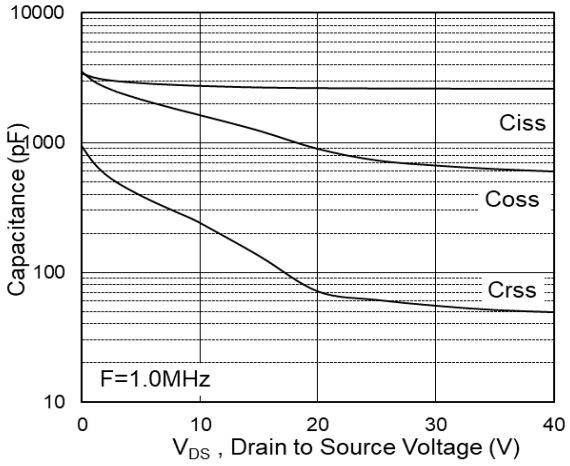


Fig.7 Capacitance

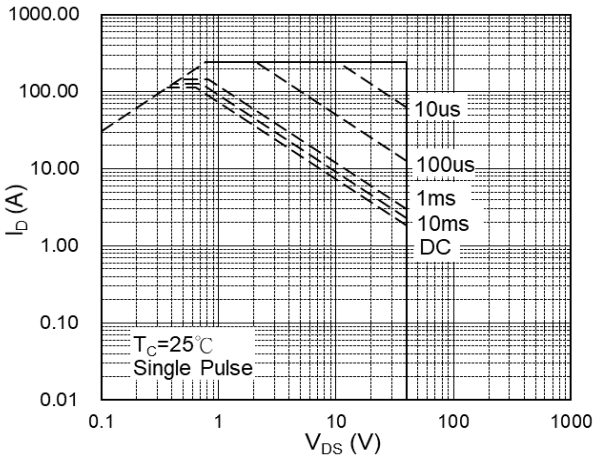


Fig.8 Safe Operating Area

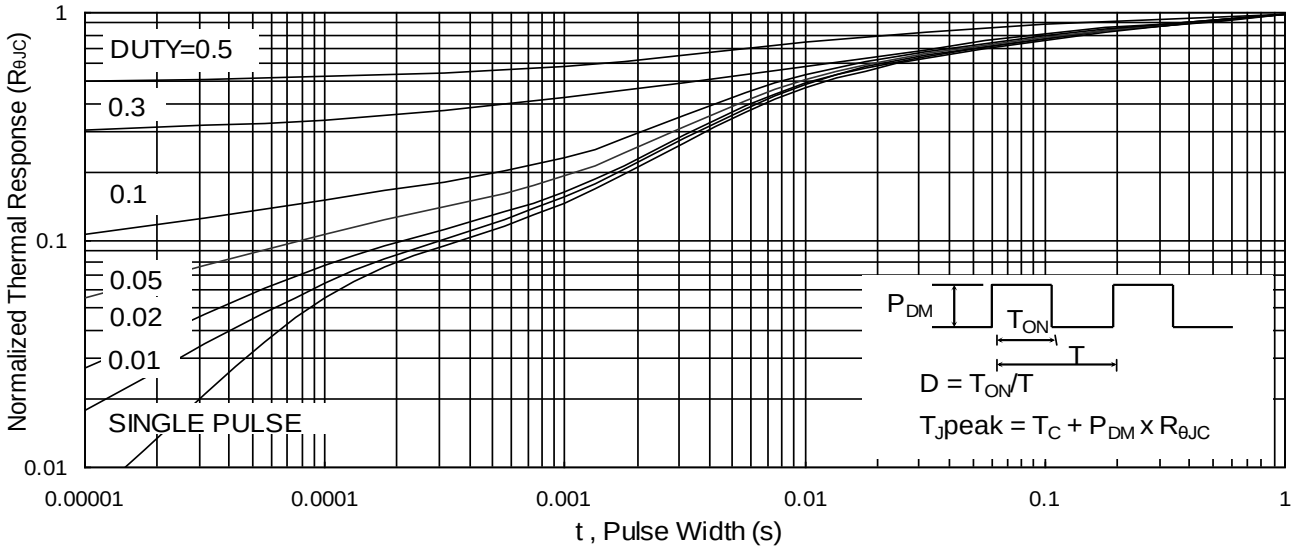
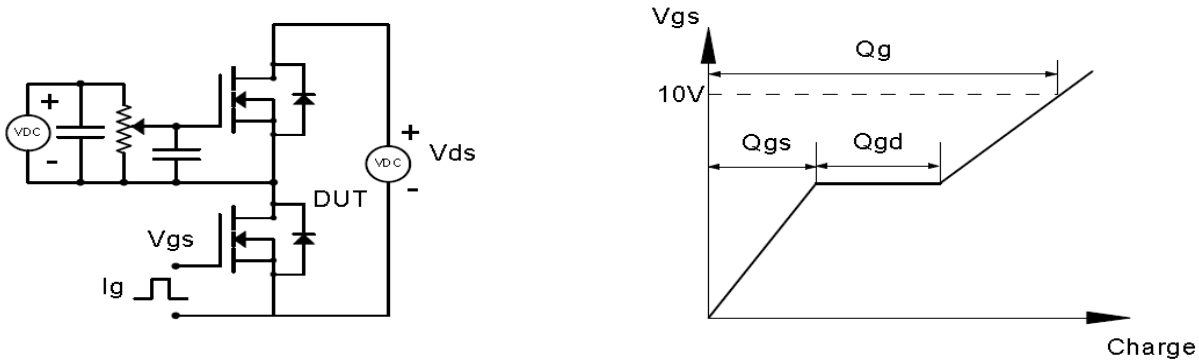


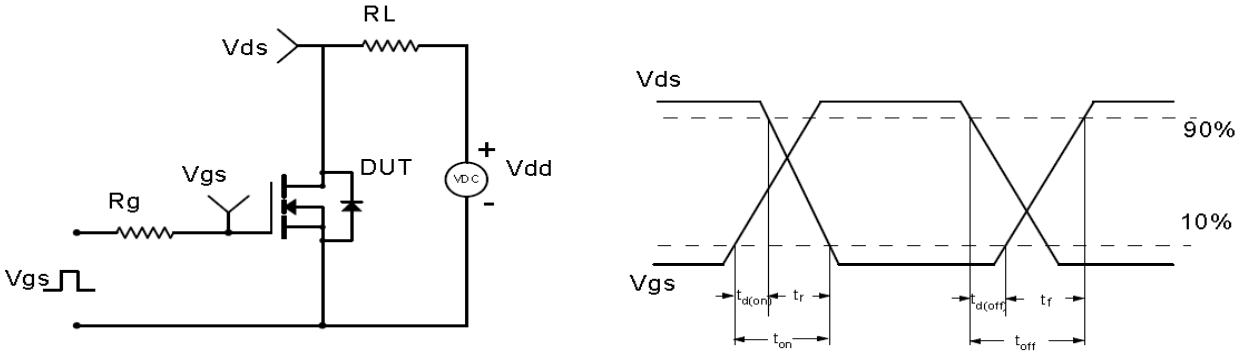
Fig.9 Normalized Maximum Transient Thermal Impedance

Test Circuit & Waveform

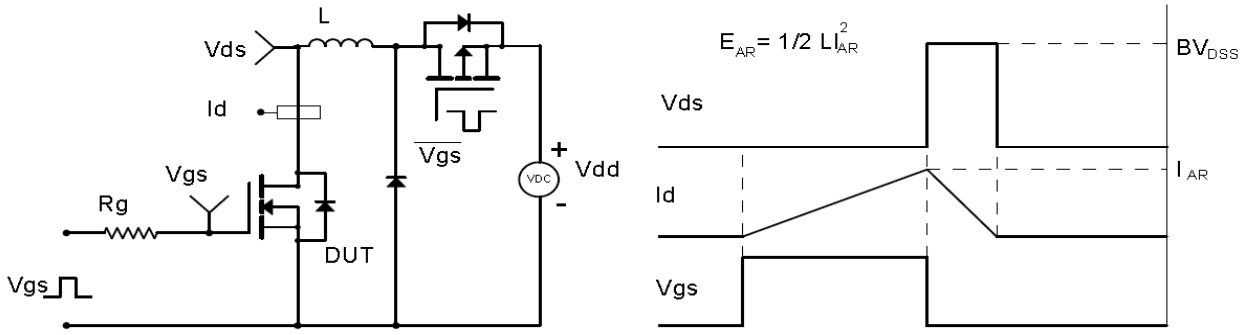
Gate Charge Test Circuit & Waveform



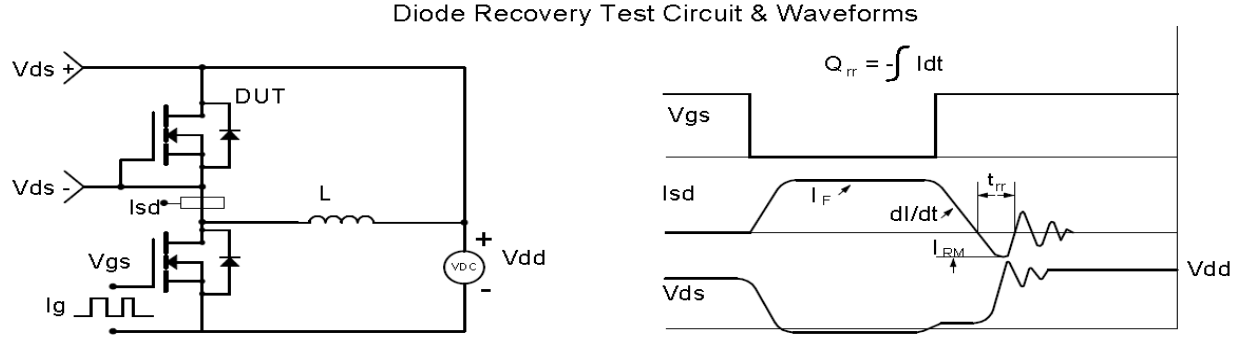
Resistive Switching Test Circuit & Waveforms



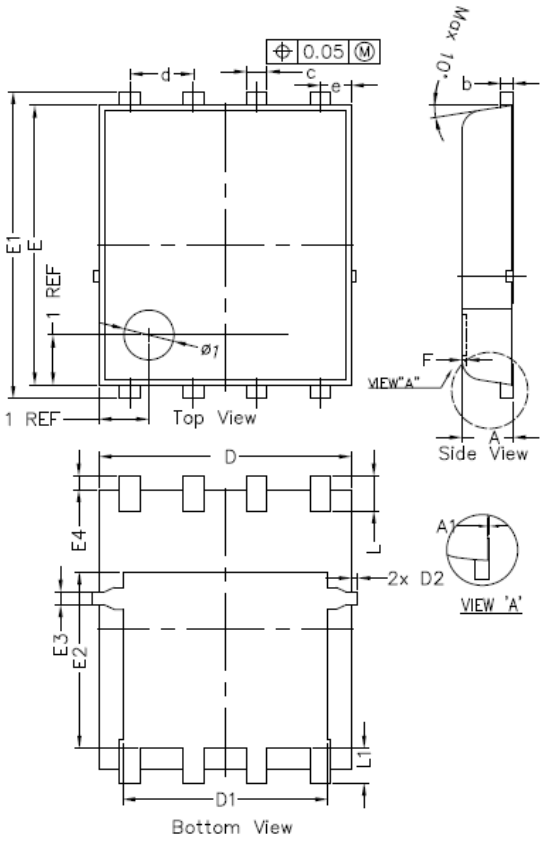
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Outline Drawing PDFN5060



Dim	Millimeters		
	Min	Nom	Max
A	0.900	1.000	1.100
A1	0.000	---	0.050
b	0.246	0.254	0.312
c	0.310	0.410	0.510
d		1.27BSC	
D	4.950	5.050	5.150
D1	4.000	4.100	4.200
D2	---	---	0.125
e		0.62BSC	
E	5.500	5.600	5.700
E1	6.050	6.150	6.250
E2	3.425	3.525	3.625
E3	0.150	0.250	0.350
E4	0.175	0.275	0.375
F	---	---	0.100
L	0.500	0.600	0.700
L1	0.600	0.700	0.800

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